INTEGRATED CIRCUITS



Product specification Replaces data of 1990 Aug 20 IC17 Data Handbook

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Philips Semiconductors





SA5209

DESCRIPTION

The SA5209 represents a breakthrough in monolithic amplifier design featuring several innovations. This unique design has combined the advantages of a high speed bipolar process with the proven Gilbert architecture.

The SA5209 is a linear broadband RF amplifier whose gain is controlled by a single DC voltage. The amplifier runs off a single 5 volt supply and consumes only 40mA. The amplifier has high impedance (1k Ω) differential inputs. The output is 50 Ω differential. Therefore, the 5209 can simultaneously perform AGC, impedance transformation, and the balun functions.

The dynamic range is excellent over a wide range of gain setting. Furthermore, the noise performance degrades at a comparatively slow rate as the gain is reduced. This is an important feature when building linear AGC systems.

FEATURES

- Gain to 1.5GHz
- 850MHz bandwidth
- High impedance differential input
- 50Ω differential output
- Single 5V power supply
- 0 1V gain control pin
- >60dB gain control range at 200MHz
- 26dB maximum gain differential
- Exceptional V_{CONTROL} / V_{GAIN} linearity
- 7dB noise figure minimum
- Full ESD protection
- Easily cascadable

ORDERING INFORMATION

DESCRIPTION	TEMPERATURE RANGE	ORDER CODE	DWG #
16-Pin Plastic Small Outline (SO) package	-40 to +85°C	SA5209D	SOT109-1
16-Pin Plastic Dual In-Line Package (DIP)	-40 to +85°C	SA5209N	SOT38-4

PIN CONFIGURATION



Figure 1. Pin Configuration

APPLICATIONS

- Linear AGC systems
- Very linear AM modulator
- RF balun
- Cable TV multi-purpose amplifier
- Fiber optic AGC
- RADAR
- User programmable fixed gain block
- Video
- Satellite receivers
- Cellular communications

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ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNITS			
V _{CC}	Supply voltage	-0.5 to +8.0	V			
PD	Power dissipation, T _A = 25ºC (still air) ¹ 16-Pin Plastic DIP 16-Pin Plastic SO	1450 mW 1100 mW				
T _{JMAX}	Maximum operating junction temperature	150	°C			
T _{STG}	Storage temperature range	-65 to +150	°C			

NOTES:

1. Maximum dissipation is determined by the operating ambient temperature and the thermal resistance, θ_{JA} :

16-Pin DIP: $\theta_{JA} = 85^{\circ}C/W$

16-Pin SO: $\theta_{JA} = 110^{\circ}$ C/W

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	RATING	UNITS
V _{CC}	Supply voltage	$V_{CC1} = V_{CC2} = 4.5 \text{ to } 7.0 \text{V}$	V
T _A	Operating ambient temperature range SA Grade	-40 to +85	°C
TJ	Operating junction temperature range SA Grade	-40 to +105	°C

DC ELECTRICAL CHARACTERISTICS

 $T_A = 25^{\circ}C$, $V_{CC1} = V_{CC2} = +5V$, $V_{AGC} = 1.0V$, unless otherwise specified.

SYMBOL	PARAMETER	TEST CONDITIONS					
STIVIDUL	FARAMETER	TEST CONDITIONS	MIN	TYP	MAX		
	Querra la compact	DC tested	38	43	48		
Icc	Supply current	Over temperature ¹	30		55	- mA	
Av	Voltage gain (single-ended in/single-ended out)	DC tested, $R_L = 10k\Omega$	17	19	21	dB	
AV	voltage gain (single-ended in/single-ended out)	Over temperature ¹	16		22	uв	
Av	Voltage gain (single-ended in/differential out)	DC tested, $R_L = 10k\Omega$	23	25	27	dB	
$\neg V$	voltage gain (single-ended invallerential out)	Over temperature ¹	22		28	UD UD	
Б	Input registeres (single anded)	DC tested at ±50µA	0.9	1.2	1.5	kΩ	
R _{IN}	Input resistance (single-ended) Over temperature ¹	Over temperature ¹	0.8		1.7	K12	
		DC tested at ±1mA	40	60	75		
R _{OUT}	Output resistance (single-ended)	Over temperature ¹	35		90	Ω	
M	Output offect veltere (output referred)			<u>+</u> 20	±100	mV	
V _{OS}	Output offset voltage (output referred)	Over temperature ¹			±250		
			1.6	2.0	2.4		
V _{IN}	DC level on inputs	Over temperature ¹	1.4		2.6	V	
			1.9	2.4	2.9		
Vout	DC level on outputs	Over temperature ¹	1.7		3.1	- V	
DODD	Output offset supply rejection ratio		20	45			
PSRR	(output referred)	Over temperature ¹	15			dB	
V _{BG}	Bandgap reference voltage	4.5V <v<sub>CC<7V R_{BG} = 10kΩ</v<sub>	1.2	1.32	1.45	V	
-		Over temperature ¹	1.1		1.55	1	

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DC ELECTRICAL CHARACTERISTICS

 $T_A = 25^{o}C$, $V_{CC1} = V_{CC2} = +5.0V$, $V_{AGC} = 1.0V$, unless otherwise specified.

SYMBOL	PARAMETER	TEST CONDITIONS				
STMIDUL	FARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	
R _{BG}	Bandgap loading	Over temperature ¹	2	10		kΩ
V _{AGC}	AGC DC control voltage range	Over temperature ¹		0-1.3		V
	AGC pin DC bias current	0V <v<sub>AGC<1.3V</v<sub>		-0.7	-6	μA
BAGC	AGC pin DC bias current	Over temperature ¹			-10	μΑ

NOTES:

1. "Over Temperature Range" testing is as follows:

SA is -40 to +85°C

At the time of this data sheet release, the D package over-temperature data sheet limits are guaranteed via guardbanded room temperature testing only.

AC ELECTRICAL CHARACTERISTICS

 $T_A = 25^{\circ}C$, $V_{CC1} = V_{CC2} = +5.0V$, $V_{AGC} = 1.0V$, unless otherwise specified.

SYMBOL	PARAMETER	TEST CONDITIONS				
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	
BW	2dD honduidth		600	850		
BW	-3dB bandwidth	Over temperature ¹	500			- MHz
GF		DC - 500MHz		<u>+</u> 0.4		dB
GF	Gain flatness	Over temperature ¹		<u>+</u> 0.6		
V _{IMAX}	Maximum input voltage swing (single-ended) for linear operation ²			200		mV _{P-P}
<i>\</i> /	Maximum output voltage swing (single-ended)	$R_L = 50\Omega$		400		mV _{P-P}
V _{OMAX}	for linear operation ²	$R_L = 1k\Omega$		1.9		V _{P-P}
NF	Noise figure (unmatched configuration)	R _S = 50Ω, f = 50MHz		9.3		dB
V _{IN-EQ}	Equivalent input noise voltage spectral density	f = 100MHz		2.5		nV/√Hz
S12	Reverse isolation	f = 100MHz	-60			dB
$\Delta G / \Delta V_{CC}$	Gain supply sensitivity (single-ended)			0.3		dB/V
$\Delta G / \Delta T$	Gain temperature sensitivity	$R_L = 50\Omega$		0.013		dB/°C
C _{IN}	Input capacitance (single-ended)			2		pF
BWAGC	-3dB bandwidth of gain control function			20		MHz
P _{O-1dB}	1dB gain compression point at output	f = 100MHz		-3		dBm
P _{I-1dB}	1dB gain compression point at input	f = 100MHz, V _{AGC} =0.1V	-10			dBm
IP3 _{OUT}	Third-order intercept point at output	f = 100MHz, V _{AGC} >0.5V		+13		dBm
IP3 _{IN}	Third-order intercept point at input	intercept point at input f = 100MHz, V _{AGC} +5		+5		dBm
ΔG_{AB}	Gain match output A to output B	f = 100MHz, V _{AGC} = 1V		0.1		dB

NOTE:

1. "Over Temperature Range" testing is as follows:

SA is -40 to +85°C

At the time of this data sheet release, the D package over-temperature data sheet limits are guaranteed via guardbanded room temperature testing only.

2. With $R_L > 1k\Omega$, overload occurs at input for single-ended gain < 13dB and at output for single-ended gain > 13dB. With $R_L = 50\Omega$, overload occurs at input for single-ended gain < 6dB and at output for single-ended gain > 6dB.

SA5209 APPLICATIONS

The SA5209 is a wideband variable gain amplifier (VGA) circuit which finds many applications in the RF, IF and video signal processing areas. This application note describes the operation of the circuit and several applications of the VGA. The simplified equivalent schematic of the VGA is shown in Figure 2. Transistors Q1-Q6 form the wideband Gilbert multiplier input stage which is biased by current source I1. The top differential pairs are biased from a buffered and level-shifted signal derived from the VAGC input and the RF input appears at the lower differential pair. The circuit topology and layout offer low input noise and wide bandwidth. The second stage is a differential transimpedance stage with current feedback which maintains the wide bandwidth of the input stage. The output stage is a pair of emitter followers with 50Ω output impedance. There is also an on-chip bandgap reference with buffered output at 1.3V, which can be used to derive the gain control voltage.

Both the inputs and outputs should be capacitor coupled or DC isolated from the signal sources and loads. Furthermore, the two inputs should be DC isolated from each other and the two outputs should likewise be DC isolated from each other. The SA5209 was designed to provide optimum performance from a 5V power source. However, there is some range around this value (4.5 - 7V) that can be used.

The input impedance is about $1k\Omega$. The main advantage to a differential input configuration is to provide the balun function. Otherwise, there is an advantage to common mode rejection, a specification that is not normally important to RF designs. The source impedance can be chosen for two different performance characteristics: Gain, or noise performance. Gain optimization will be realized if the input impedance is matched to about $1k\Omega$. A 4:1 balun will provide such a broadband match from a 50Ω source. Noise performance will be optimized if the input impedance is matched to about 200Ω. A 2:1 balun will provide such a broadband match from a 50 Ω source. The minimum noise figure can then be expected to be about 7dB. Maximum gain will be about 23dB for a single-ended output. If the differential output is used and properly matched, nearly 30dB can be realized. With gain optimization, the noise figure will degrade to about 8dB. With no matching unit at the input, a 9dB noise figure can be expected from a 50Ω source. If the source is terminated, the noise figure will increase to about 15dB. All these noise figures will occur at maximum gain.

The SA5209 has an excellent noise figure vs gain relationship. With any VGA circuit, the noise performance will degrade with decreasing

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gain. The 5209 has about a 1.2dB noise figure degradation for each 2dB gain reduction. With the input matched for optimum gain, the 8dB noise figure at 23dB gain will degrade to about a 20dB noise figure at 0dB gain.

The SA5209 also displays excellent linearity between voltage gain and control voltage. Indeed, the relationship is of sufficient linearity that high fidelity AM modulation is possible using the SA5209. A maximum control voltage frequency of about 20MHz permits video baseband sources for AM.

A stabilized bandgap reference voltage is made available on the SA5209 (Pin 7). For fixed gain applications this voltage can be resistor divided, and then fed to the gain control terminal (Pin 8). Using the bandgap voltage reference for gain control produces very stable gain characteristics over wide temperature ranges. The gain setting resistors are not part of the RF signal path, and thus stray capacitance here is not important.

The wide bandwidth and excellent gain control linearity make the SA5209 VGA ideally suited for the automatic gain control (AGC) function in RF and IF processing in cellular radio base stations, Direct Broadcast Satellite (DBS) decoders, cable TV systems, fiber optic receivers for wideband data and video, and other radio communication applications. A typical AGC configuration using the SA5209 is shown in Figure 3. Three SA5209s are cascaded with appropriate AC coupling capacitors. The output of the final stage drives the full-wave rectifier composed of two UHF Schottky diodes BAT17 as shown. The diodes are biased by R1 and R2 to V_{CC} such that a quiescent current of about 2mA in each leg is achieved. An SA5230 low voltage op amp is used as an integrator which drives the VAGC pin on all three SA5209s. R3 and C3 filter the high frequency ripple from the full-wave rectified signal. A voltage divider is used to generate the reference for the non-inverting input of the op amp at about 1.7V. Keeping D3 the same type as D1 and D2 will provide a first order compensation for the change in Schottky voltage over the operating temperature range and improve the AGC performance. R6 is a variable resistor for adjustments to the op amp reference voltage. In low cost and large volume applications this could be replaced with a fixed resistor, which would result in a slight loss of the AGC dynamic range. Cascading three SA5209s will give a dynamic range in excess of 60dB.

The SA5209 is a very user-friendly part and will not oscillate in most applications. However, in an application such as with gains in excess of 60dB and bandwidth beyond 100MHz, good PC board layout with proper supply decoupling is strongly recommended.



Figure 2. Equivalent Schematic of the VGA



Figure 3. AGC Configuration Using Cascaded SA5209s



Figure 4. VGA AC Evaluation Board



Figure 5. Broadband Noise Optimization







Figure 7. Broadband Gain Optimization











Figure 10. Unterminated Configuration



Figure 11. User-Programmable Fixed Gain Block



Figure 12. AM Modulator







Figure 14. Test Set-up 1 (Used for all Graphs)



Figure 15. Gain vs V_{AGC} and V_{CC}



Figure 16. Insertion Gain vs $V_{\mbox{AGC}}$ and Temperature



Figure 17. Voltage Gain vs Temperature and V_{CC}



Figure 18. Supply Current vs Temperature and $V_{\mbox{CC}}$



Figure 19. Input Resistance vs Temperature







Figure 21. Output Bias Voltage vs Temperature and $\rm V_{CC}$



Figure 22. DC Output Swing vs Temperature



Figure 23. Insertion Gain vs Frequency and $V_{\mbox{AGC}}$



Figure 24. Insertion Gain vs Frequency and $V_{\mbox{CC}}$



Figure 25. Insertion Gain vs Temperature and V_{CC}



Figure 26. Output Return Loss vs Frequency



Figure 27. Reverse Isolation vs Frequency



Figure 28. 1dB Gain Compression vs $V_{\mbox{AGC}}$



Figure 29. Third-Order Intermodulation Intercept vs $V_{\mbox{AGC}}$



Figure 30. Noise Figure vs V_{AGC}



Figure 31. Noise Figure vs Frequency



Figure 32. Bandgap Voltage vs Temperature and $\ensuremath{\mathsf{V_{CC}}}$



Figure 33. Fixed Gain vs Temperature



Figure 34. VGA AC Evaluation Board Layout



Figure 35. AGC Configuration Using Cascaded SA5209s - Layout



Figure 36. VGA AC Evaluation Board Layout (DIP Package)





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UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	c	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	M _H	w	max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.020	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.030

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT38-4						-92-11-17- 95-01-14

Product specification

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SOT38-4

SA5209

DEFINITIONS						
Data Sheet Identification	Definition					
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.				
Preliminary Specification	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.				
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